

Supporting Information for

High-performance photodetectors based on bandgap engineered novel layer GaSe_{0.5}Te_{0.5} nanoflakes

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Fig. S1. The photograph of peeled off sample from quartz tube.

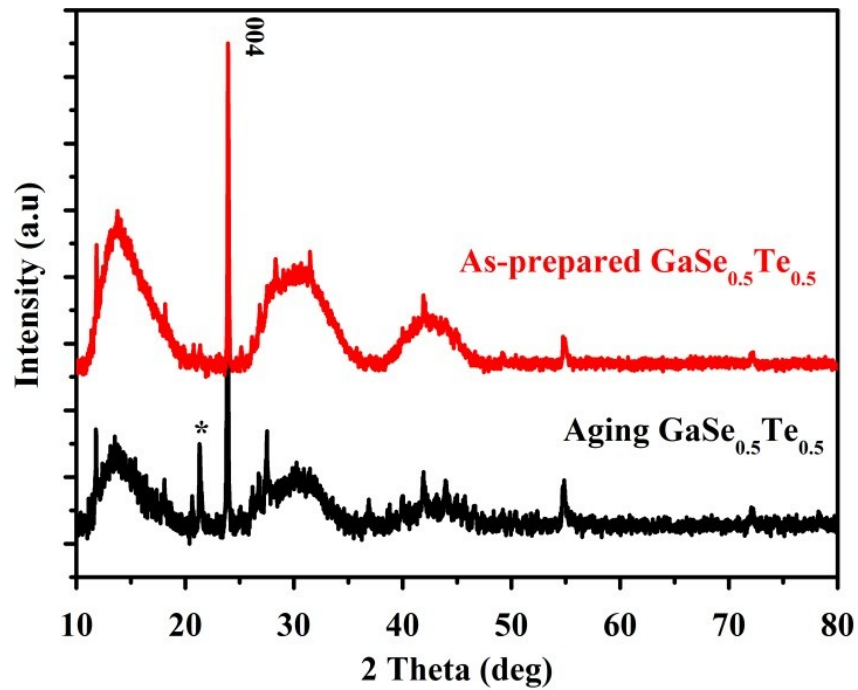


Fig. S2. XRD of peeled off sample. The aging sample was stored in dark condition for several months. The diffraction peak masked with * is the oxide of GaSe_{0.5}Te_{0.5}.

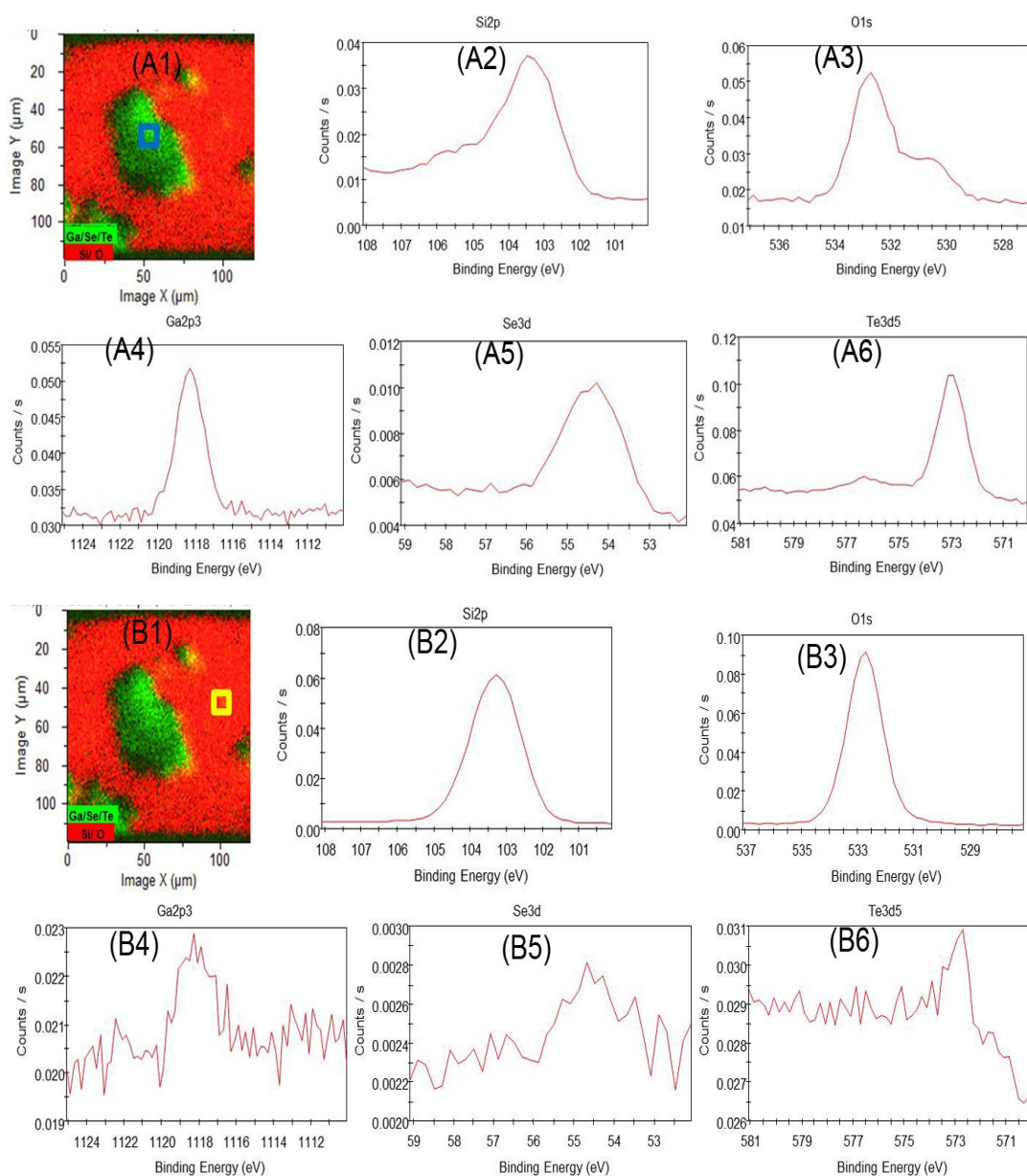


Figure S3. (A1-A6) XPS and corresponding overlaid image of single GaSe_{0.5}Te_{0.5} nanoflake (blue marked area). (B1-B6) XPS and corresponding overlaid image SiO₂/Si substrate (yellow marked area).